IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:	§	
Hans Norström et al.	§	Group Art Unit:
	§	
Serial No.:	§	Examiner:
	§	
Filing Date: **April 21, 2004**	§	
	§	Attny. Docket No. **068758.0182**
Title: **Silicon-Germanium Mesa Transistor**	§	Client Ref.: **P14802US1/RF/HS**

Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

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PURSUANT TO 37 C.F.R. § 1.10, I HEREBY CERTIFY THAT I HAVE INFORMATION AND A REASONABLE BASIS FOR BELIEF THAT THIS CORRESPONDENCE WILL BE DEPOSITED WITH THE U.S. POSTAL SERVICE AS EXPRESS MAIL POST OFFICE TO ADDRESSEE, ON THE DATE BELOW, AND IS ADDRESSED TO:

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INFORMATION DISCLOSURE STATEMENT

Sir:

Applicants respectfully request, pursuant to 37 C.F.R. §§1.56, 1.97 and 1.98, that the art listed on the attached PTO-1449 form be considered and cited in the examination of the above-identified application. A copy of the cited art is enclosed for the convenience of the Examiner.

Furthermore, pursuant to 37 C.F.R. §§1.97(g) and (h), no representation is made that these references are material to the patentability of the present application.

As the Information Disclosure Statement is being submitted before the mailing of the first office action on the merits, Applicants believe that no fee is required. If a fee is

required, please accept this transmittal as a petition therefor and charge any fee to Baker Botts L.L.P. *(formerly, Baker & Botts, L.L.P.)* Deposit Account No. 02-0383, Order No. (***068758.0182***) for any other charges necessary for the filing of this Information Disclosure Statement.

BAKER BOTTS L.L.P. (023640)

Date: April 21, 2004

By: 

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PTO-1449 **Information Disclosure Citation in an Application**	Application No.	Applicant(s): **Hans Norström et al.**	
	Docket Number **068758.0182**	Group Art Unit	Filing Date **April 21, 2004**

U.S. PATENT DOCUMENTS

		DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
	1	5,587,327	12-24-96	König et al.	437	31	05-23-95
	2	5,821,149	10-13-98	Schüppen et al.	438	312	03-14-97
	3	6,251,738	06-26-01	Huang	438	312	01-10-00

FOREIGN PATENT DOCUMENTS

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
	4	DE 196 52 423 A1	06-10-98	GERMANY	H01L	29/737		x
	5	SE 0101567-6	12-23-02	SWEDEN	H01L	21/8249	x	
	6	EP 1 139 408 A2	01-26-01	EPO	H01L	21/331	x	
	7	WO 98/53489	11-26-98	PCT	H01L	21/331	x	
	8	WO 01/20664	03-22-01	PCT	H01L	21/76	x	

NON-PATENT DOCUMENTS

		DOCUMENT (Including Author, Title, Source, and Pertinent Pages)	DATE
	9	A Schüppen et al., "Enhanced SiGe Heterojunction Bipolar Transistors with 160 GHz-f_{max}"; IEEE IEDM Tech Dig., p. 743	1995
	10	A. Monroy et al., "BiCMOS6G: A high performance .035 μm SiGe BiCMOS technology for wireless applications", IEEE BCTM, p. 121	1999
	11	S.A. St.Onge et al., "A 0.24 μm SiGe BiCMOS Mixed-Signal RF Production Technology Featuring a 47 GHz f_t HBT and 0.18 μm L_{eff} CMOS", IEEE BCTM99, p. 117	1999
	12	John D. Cressler, "SiGe HBT Technology: A New Contender for Si-Baesd RF and Microwave Circuit Applications"; IEEE Transactions on Microwave Theory and Techniques, Vol. 46, No. 5	May 1998
	13	D. Behammer, et al.; "Si/SiGe HBTs for Application in Low Power ICs"; Solid-State Electronics, Vol. 39, No. 4, pp. 471-480	1996

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.